Product data sheet

1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses
- Fast switching
- High thermal cycling performance
- Low thermal resistance
- Low forward voltage drop

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	400	V
I _{O(AV)}	average output current	SQW; δ = 0.5; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2		-	-	20	А
Static charact	teristics						
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.87	1.05	V
Dynamic char	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}; \underline{\text{Fig. 6}}$		-	50	60	ns





Dual ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	A1 A2
2	K	cathode	 	K K
3	A2	anode 2	TO-220AB (SOT78)	sym125

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV34-400	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

Dual ultrafast power diode

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	400	V
V_{RWM}	crest working reverse voltage		-	400	V
V _R	reverse voltage	T _{mb} ≤ 138 °C; DC	-	400	V
I _{O(AV)}	average output current	SQW; δ = 0.5; $T_{mb} \le$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	-	20	Α
I _{FRM}	repetitive peak forward current	$\bar{\delta}$ = 0.5; t_p = 25 μ s; T_{mb} ≤ 115 °C; per diode	-	20	А
I _{FSM}	non-repetitive peak forward current	SIN; t_p = 10 ms; $T_{j(init)}$ = 25 °C; per diode	-	120	Α
		SIN; t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode	-	132	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

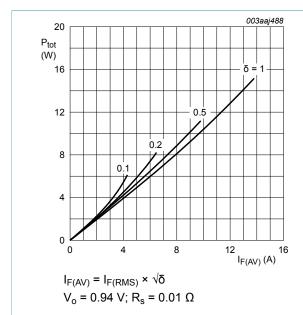


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

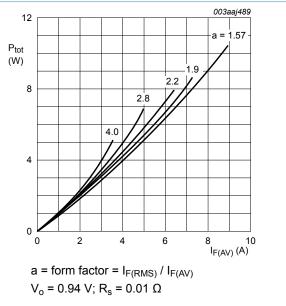


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

Dual ultrafast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; per diode; Fig. 3	-	-	2.4	K/W
mounting bas	mounting base	with heatsink compound; both diodes conducting	-	-	1.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	60	-	K/W

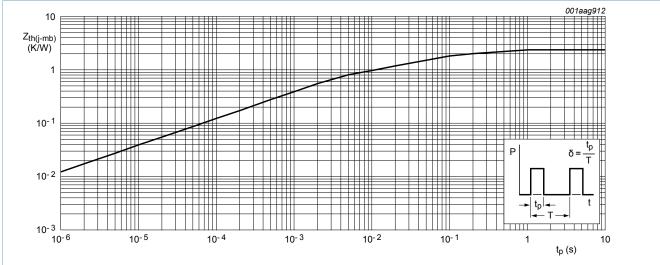


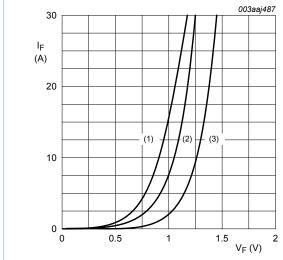
Fig. 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

Dual ultrafast power diode

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V_{F}	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.35	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.87	1.05	V
I _R	reverse current	V _R = 400 V; T _j = 25 °C	-	10	50	μΑ
		V _R = 400 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic cl	haracteristics		'			
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; Fig. 5; Fig. 6	-	50	50	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7; Fig. 6$	-	50	60	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; \underline{\text{Fig. 8}}; \underline{\text{Fig. 6}}$	-	4	5	Α
V_{FRM}	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; T_j = 25 °C;$ Fig. 9	-	2.5	-	V



 $V_0 = 0.94 \text{ V}; R_s = 0.01 \Omega$

(1) T_i = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 4. Forward current as a function of forward voltage; per diode

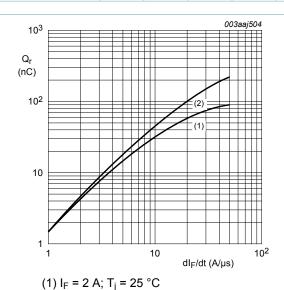


Fig. 5. Recovered charge as a function of rate of change of forward current; per diode; maximum values

(2) $I_F = 20 \text{ A}; T_j = 25 ^{\circ}\text{C}$

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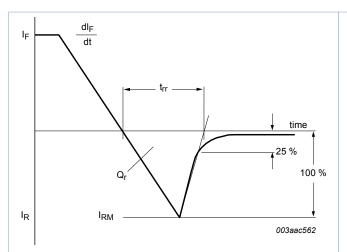
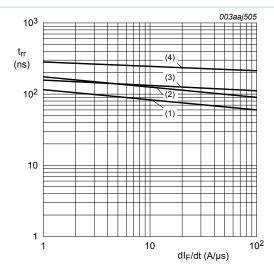


Fig. 6. Reverse recovery definitions; ramp recovery



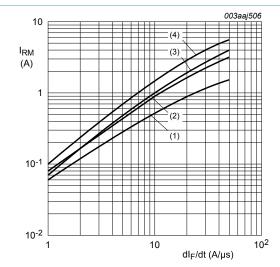
(1)
$$I_F = 1 A$$
; $T_j = 25 °C$

(2)
$$I_F = 1 A$$
; $T_j = 100 \, ^{\circ}C$

(3)
$$I_F = 20 \text{ A}; T_j = 25 ^{\circ}\text{C}$$

(4)
$$I_F = 20 \text{ A}; T_j = 100 \,^{\circ}\text{C}$$

Fig. 7. Reverse recovery time as a function of rate of change of forward current; per diode; maximum values



(1) $I_F = 1 A$; $T_j = 25 °C$

(2)
$$I_F = 1 A$$
; $T_i = 100 °C$

(3)
$$I_F = 20 \text{ A}$$
; $T_i = 25 \,^{\circ}\text{C}$

(4)
$$I_F = 20 \text{ A}$$
; $T_j = 100 \,^{\circ}\text{C}$

Fig. 8. Peak reverse recovery current as a function of rate of change of forward current; per diode; maximum values

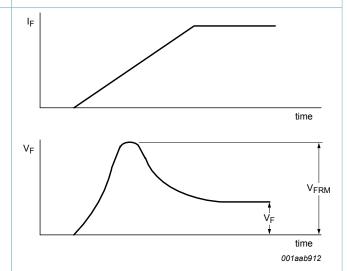
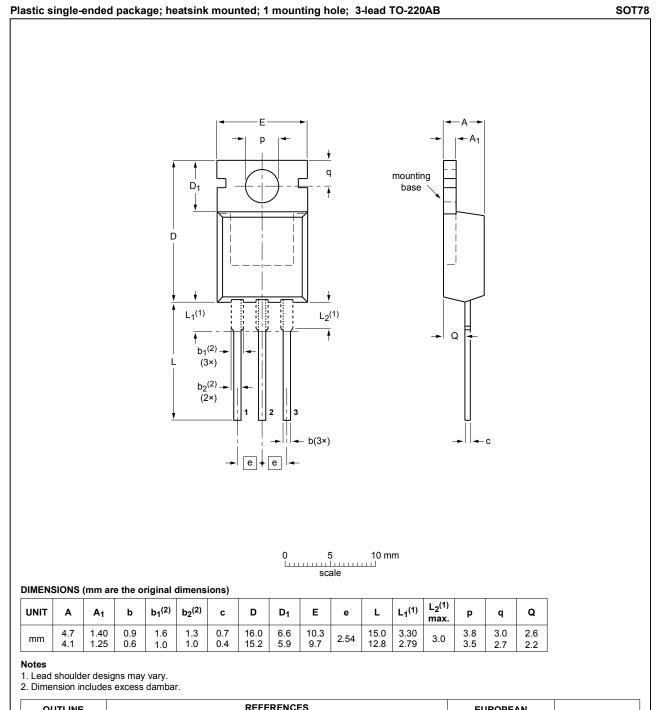


Fig. 9. Forward recovery definitions

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10. Package outline



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig. 10. Package outline TO-220AB (SOT78)

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Date of release: 4 June 2014